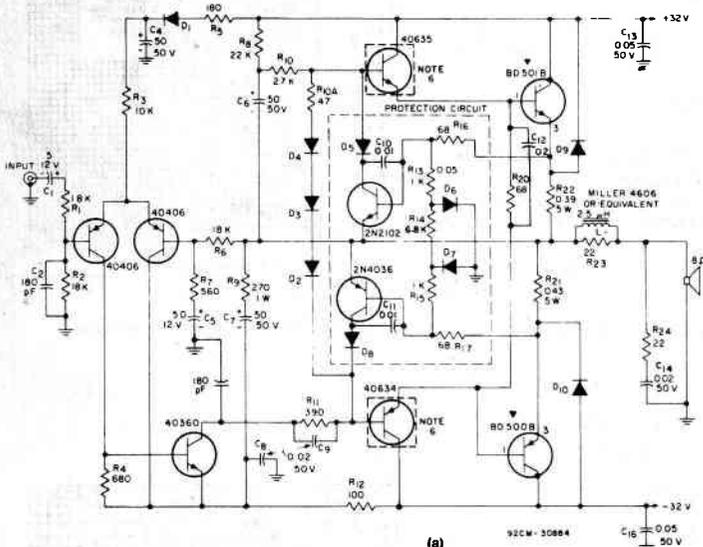


BD500, BD501 Series

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C

CHARACTERISTICS	TEST CONDITIONS	LIMITS [▲]						UNITS	
		BD500* BD501		BD500A* BD501A		BD500B* BD501B			
		Min.	Max.	Min.	Max.	Min.	Max.		
I_{CER} $R_{BE} = 100 \Omega$	$V_{CE} = 45 V$ $V_{CE} = 55 V$ $V_{CE} = 75 V$	—	1	—	—	—	—	mA	
I_{EBO}	$V_{EB} = 5 V$	—	1	—	1	—	1	mA	
V_{CEO}	$I_C = 0.1 A$	50	—	60	—	80	—	V	
V_{CER}	$I_C = 0.1 A; R_{BE} = 100 \Omega$	55	—	65	—	85	—	V	
f_T	$I_C = 0.5 A; V_{CE} = 4 V$	5	—	5	—	5	—	MHz	
h_{FE}	$I_C = 5 A; V_{CE} = 4 V$ $I_C = 3.5 A; V_{CE} = 4 V$	15	90	15	90	—	20	120	—
$V_{CE(sat)}$	$I_C = 5 A; I_B = 0.5 A$ $I_C = 3.5 A; I_B = 0.35 A$	—	1.2	—	1.2	—	—	1	V
V_{BE}	$I_C = 5 A; V_{CE} = 4 V$ $I_C = 3.5 A; V_{CE} = 4 V$	—	1.8	—	1.8	—	—	1.5	V
$I_{S/b}$	$V_{CE} = 20 V; t = 0.55 s$ $V_{CE} = 25 V; t = 0.55 s$ $V_{CE} = 30 V; t = 0.55 s$	3.75	—	3	—	—	—	2.5	A

[▲]For characteristics curves and test conditions, refer to published data for prototypes (File 678): 2N6487 (BD501, BD501A); 2N6488 (BD501B); 2N6490 (BD500, BD500A); 2N6491 (BD500B).
^{*}For p-n-p devices, voltage and current values are negative.



- NOTES (for Fig. 5):
- D1-D10—D1201A.
 - Resistors are 1/2-watt, $\pm 10\%$, unless otherwise specified; values are in ohms.
 - Non-inductive resistors.
 - Capacitances are in μF unless otherwise specified.
 - 55°C thermal cutout attached to heat sink of output devices.
 - TO-39 case devices with heat radiator attached.
 - Provide heat sink of approx. 1.2°C/W per output device with a contact thermal resistance of 1.3°C/W max. and $T_A = 40^\circ C$ max.

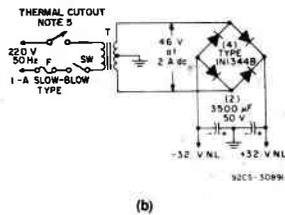


Fig. 5 - 40-watt amplifier circuit featuring full-complementary-symmetry output using load line limiting; (a) basic amplifier circuit, (b) power-supply circuit.

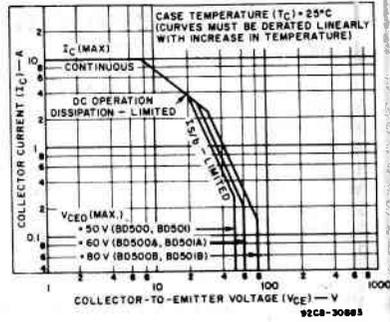


Fig. 4 - Maximum operating areas for all types.

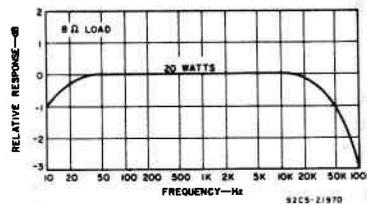


Fig. 6 - Typical frequency response.

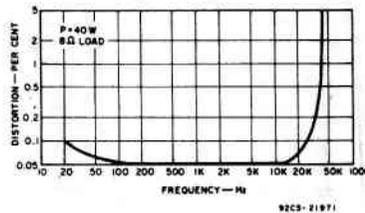


Fig. 7 - Typical total harmonic distortion as a function of frequency.

transistors for 70-
antary-Symmetry

BD500A, and BD500B are
transistors especially suitable
for audio-amplifier circuits,
and may be used as either driver

together with a variety of
input devices,
for biasing, current sources,
(for overload protection).
may be used to develop

INGS, Absolute-Maximum Val

1/32 in. (0.8 mm) from center
3X.

CHARACTERISTICS, A

TEST CONDITIONS

- $V_{CE} = 110 V$
- $V_{CE} = 175 V$
- $V_{CE} = 250 V$
- $V_{CE} = 95 V$
- $V_{CE} = 150 V$
- $V_{CE} = 200 V$

$V_{EB} = 5 V$

$I_C = 2 A$

$R_{BE} =$

$V_{CE} =$

$V_{CE} = 4$

$V_{CE} = 2 A; V_{CE} =$

$V_{CE} = 80 V; t =$

$V_{CE} = 100 V;$

$V_{CE} = 140 V$

▲ For characteristics curves and

▲ For characteristics curves and